

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE  
REFERENCE CIRCUIT

Inventor: Paul David Ranucci

Application No.: 10/730,201

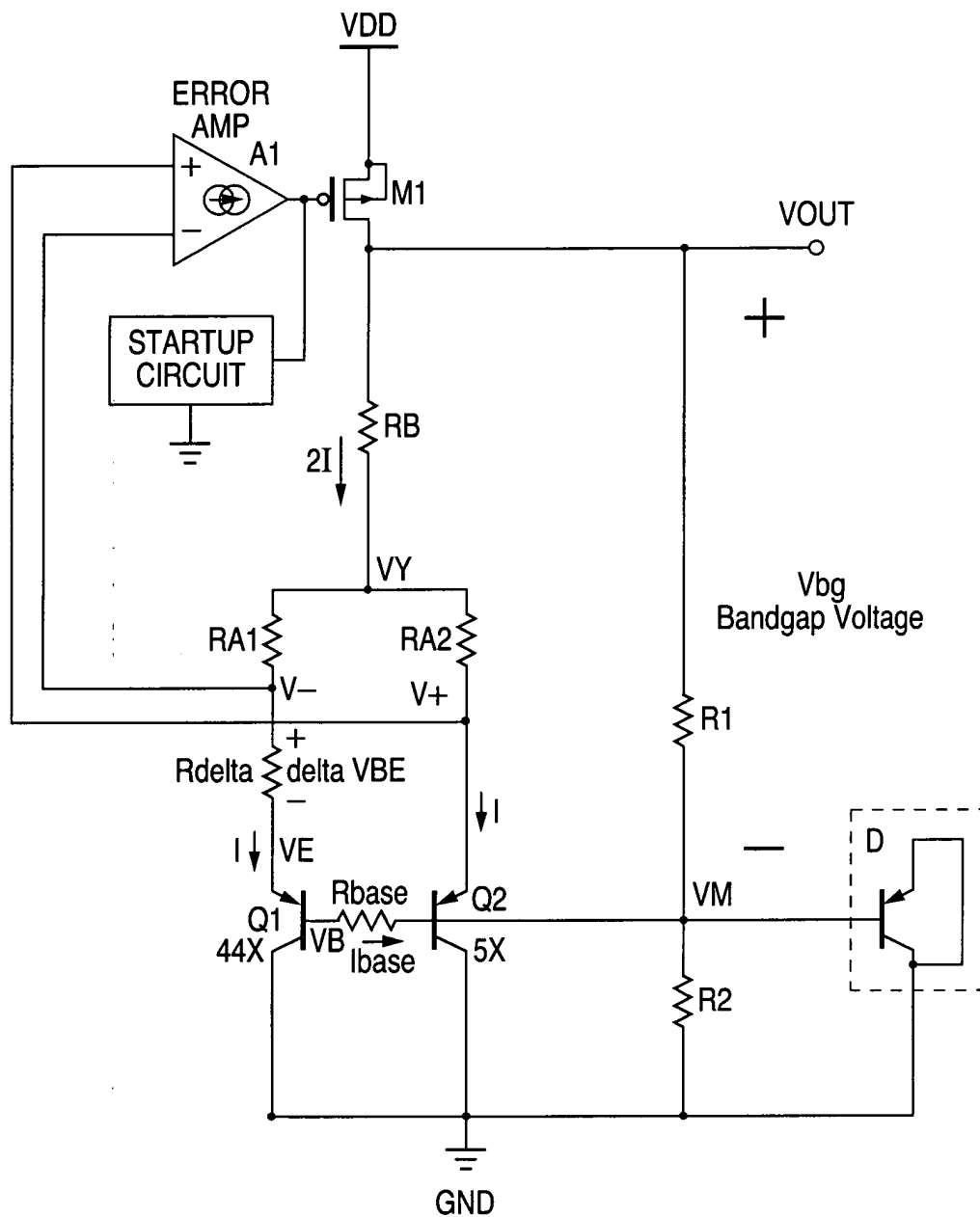


FIG. 1

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE  
REFERENCE CIRCUIT

Inventor: Paul David Ranucci

Application No.: 10/730,201

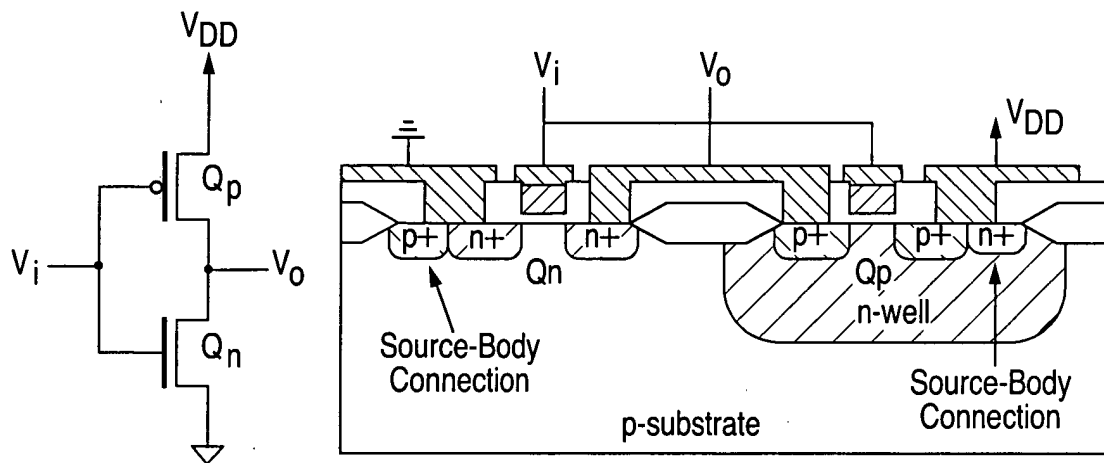


FIG. 1A

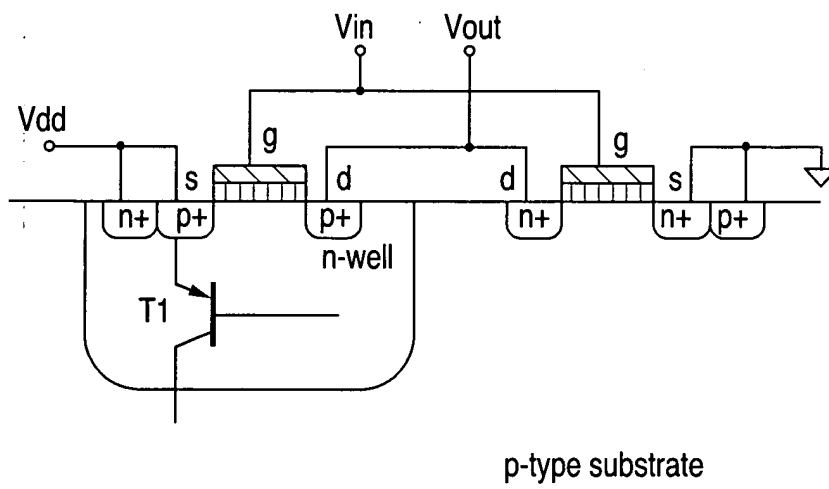


FIG. 1B

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE  
REFERENCE CIRCUIT

Inventor: Paul David Ranucci

Application No.: 10/730,201

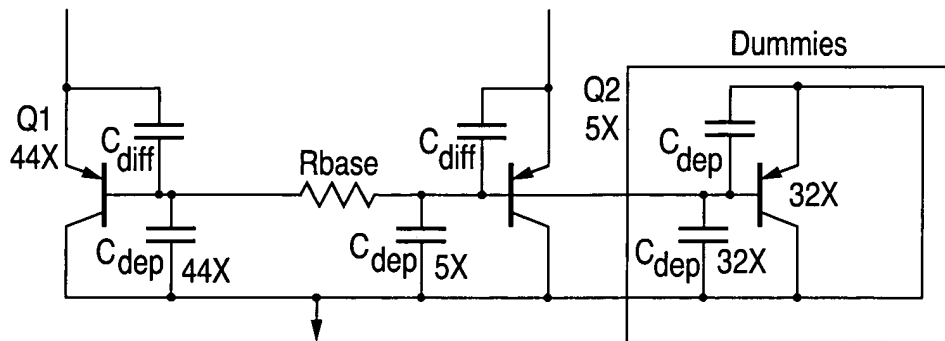


FIG. 2

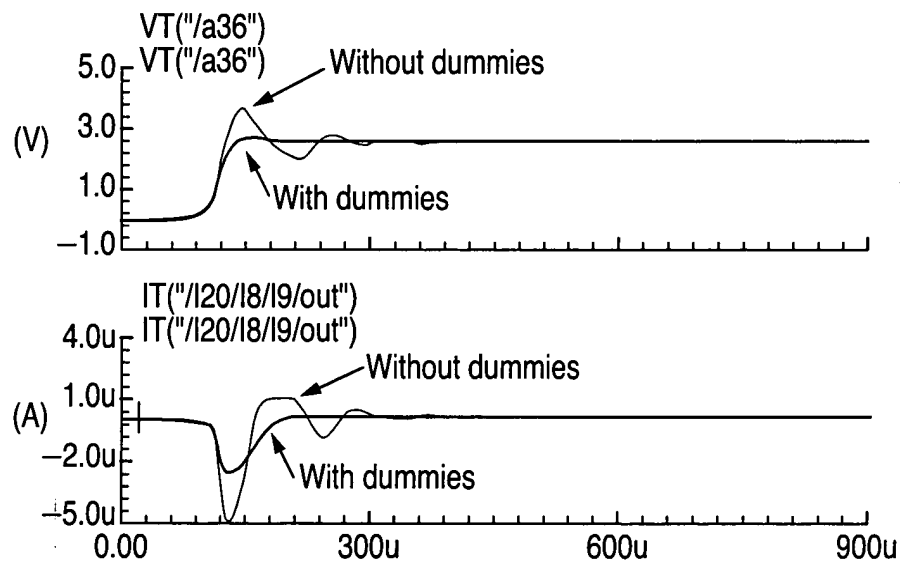


FIG. 4

METAL OXIDE SEMICONDUCTOR (MOS) BANDGAP VOLTAGE  
REFERENCE CIRCUIT

Inventor: Paul David Ranucci

Application No.: 10/730,201

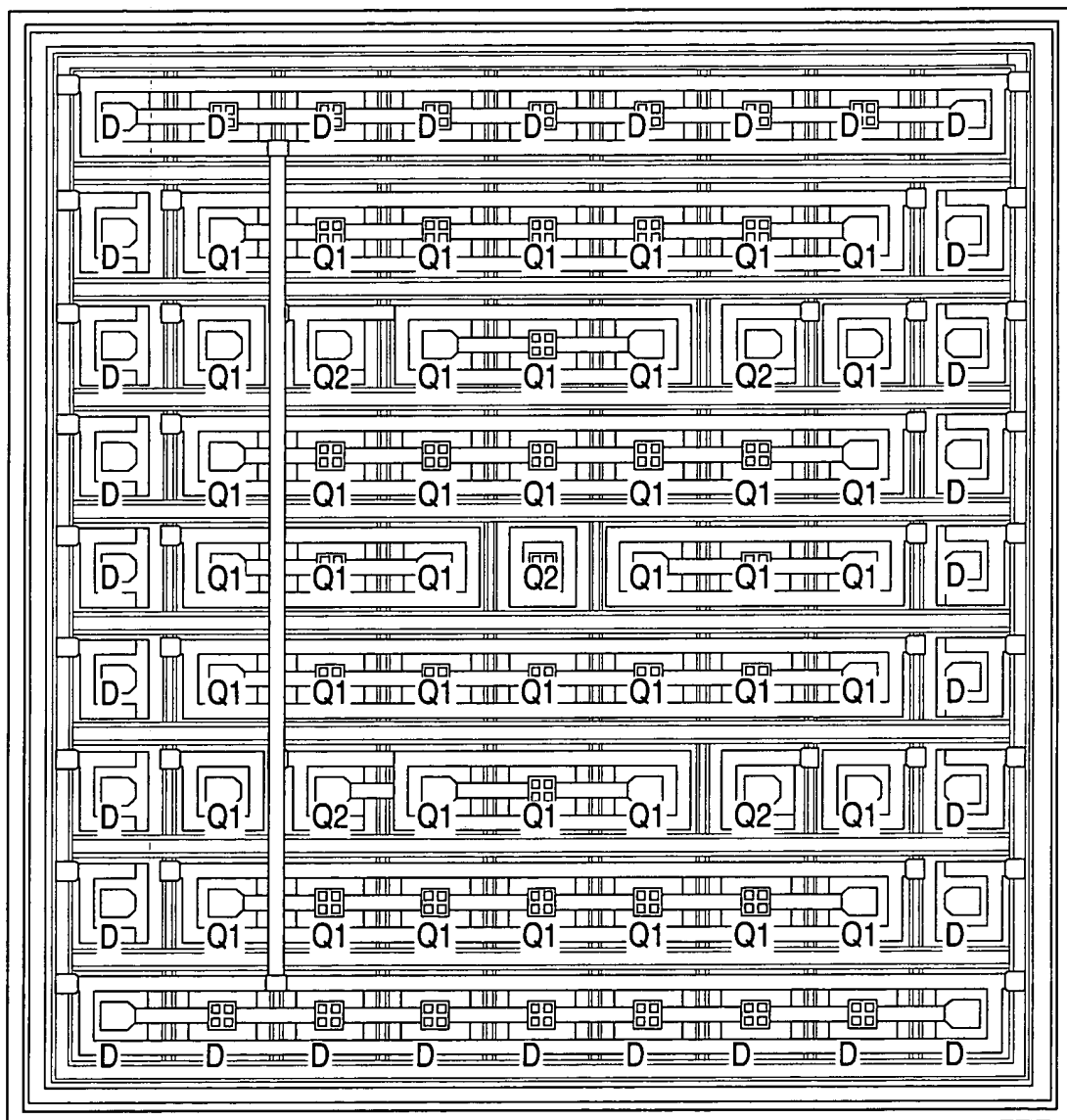


FIG. 3